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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/857,803	06/11/2001	Hiroji Aga	109725	2312

25944 7590 03/14/2002

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EXAMINER

ESTRADA, MICHELLE

ART UNIT PAPER NUMBER

2823

DATE MAILED: 03/14/2002

Please find below and/or attached an Office communication concerning this application or proceeding.

Handwritten signature or mark

<b>Office Action Summary</b>	<b>Application No.</b>	<b>Applicant(s)</b>	
	09/857,803	AGA ET AL.	
	<b>Examiner</b>	<b>Art Unit</b>	
	Michelle Estrada	2823	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

**Period for Reply**

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

**Status**

- 1) ☒ Responsive to communication(s) filed on 08 February 2002.
- 2a) ☐ This action is **FINAL**.                      2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

**Disposition of Claims**

- 4) ☒ Claim(s) 1-9 is/are pending in the application.
- 4a) Of the above claim(s) 6-9 is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 1-5 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

**Application Papers**

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.  
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on \_\_\_\_\_ is: a) ☐ approved b) ☐ disapproved by the Examiner.  
If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

**Priority under 35 U.S.C. §§ 119 and 120**

- 13) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  
a) ☐ All   b) ☐ Some \*   c) ☐ None of:  
1. ☐ Certified copies of the priority documents have been received.  
2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.  
3. ☒ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).  
\* See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).  
a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

**Attachment(s)**

- |  |   |
|--|---|
| 1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892)                                  | 4) <input type="checkbox"/> Interview Summary (PTO-413) Paper No(s). _____  |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)                         | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 3) <input checked="" type="checkbox"/> Information Disclosure Statement(s) (PTO-1449) Paper No(s) <u>4</u> . | 6) <input type="checkbox"/> Other:  |

### **DETAILED ACTION**

Applicant's election with traverse of Group I (claims 1-5) in Paper No. 8 is acknowledged. The traversal is on the ground(s) that the process need not inherently produce the product for Unity of Invention to exist. This is not found persuasive because a process is specially adapted for the manufacture of a product if it inherently results in the product (See MPEP, Appendix AI, Annex B, Part 1(e)(iii)).

The requirement is still deemed proper and is therefore made FINAL.

### ***Claim Rejections - 35 USC § 103***

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 1 and 2 are rejected under 35 U.S.C. 103(a) as being unpatentable over the combination of Yamamoto (JP-10275905) and Takada et al. (JP-10335616).

Yamamoto discloses a method for producing an SOI wafer by the hydrogen ion delamination method comprising at least a step of bonding a base wafer (5) and a bond wafer (1) having a micro bubble layer formed by gas ion implantation (See fig. 1c) and a step of delaminating a wafer having an SOI layer (2) at the micro bubble layer as a border, wherein, after the delamination step, the wafer having an SOI layer is subjected to a hydrogen RTA treatment.

Yamamoto does not disclose cooling the wafer, and a heat treatment of a batch furnace.

Takada et al. discloses a semiconductor substrate (11); forming an insulating layer (11a); implanting hydrogen ions into the semiconductor surface; semiconductor substrate (11) is joined to a support substrate (12); the resulting structure is subject to thermal treatment for delamination; and after delamination the laminate (13) is subjected to a thermal treatment (See abstract). The combination teaches annealing by either furnace or RTA. It would have been within the scope of one of ordinary skill in the art to use either one (furnace or RTA) for the first part of the heating step and the other one for the rest of the heating step. A cooling step would occur after RTA treatment upon removal of the light source.

It would have been within the scope of one of ordinary skill in the art to use thermal treatment of Takada et al. for its disclosed intended purpose to achieve the heat treatment of Yamamoto.

Claims 3-5 are rejected under 35 U.S.C. 103(a) as being unpatentable over the combination of Yamamoto (JP-10275905) and Takada et al. (JP-10335616) as applied to claims 1 and 2 above, and further in view of applicant's admitted prior art and Wolf et al. (Vol. 1).

The combination does not disclose that the wafer is a CZ wafer of which COPs (Crystal Originated Particles) at least on surface are reduced is used as the bond wafer, and that the CZ wafer is produced from a single crystal ingot.

Wolf et al. (Vol. 1) discloses that the CZ wafer can be produced from a single crystal ingot (See pages 23-25).

It would have been within the scope of one of ordinary skill in the art to combine the teachings of the combination, Applicant's admitted prior art and Wolf et al. to enable the bond wafer of the combination to be provided.

Applicant's admitted prior art discloses a wafer which is a CZ wafer of which COPs (Crystal Originated Particles) at least on surface are reduced which is used as the bond wafer (See pages 4 and 5 of the disclosure). It would have been within the scope of one of ordinary skill in the art to employ the CZ wafer of applicant's admitted prior art and Wolf et al. for its disclosed intended purpose to provide the bond wafer of the combination.


Wolf et al. (Vol. 1) discloses that the CZ wafer can be produced from a single crystal ingot (See pages 23-25).

It would have been within the scope of one of ordinary skill in the art to produce the CZ wafer of Wolf (Vol. 1) for its disclosed intended purpose to achieve the bonding step of the combination.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Michelle Estrada whose telephone number is 703-308-0729. The examiner can normally be reached on Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on 703-308-4918. The fax phone numbers for the organization where this application or proceeding is assigned are 703-308-7722 (7724, 3431 and 3432) for regular communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.



George Fourson  
Primary Examiner  
Art Unit 2823



MEstrada

March 11, 2002